

SEMITOP® 3

IGBT Module

SK60GB128

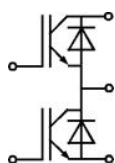
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- High short circuit capability
- SPT= Soft-Punch-Through technology
- $V_{ce,sat}$ with positive coefficient

Typical Applications*

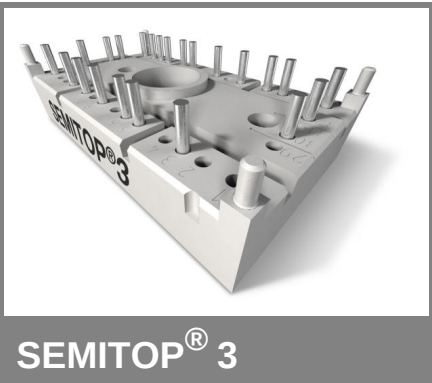
- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



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Absolute Maximum Ratings		T _s = 25 °C, unless otherwise specified		
Symbol	Conditions		Values	Units
IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	T _j = 125 °C	T _s = 25 °C	63	A
		T _s = 80 °C	44	A
I _{CRM}	I _{CRM} = 2 x I _{Cnom}		100	A
V _{GES}			± 20	V
t _{psc}	V _{CC} = 600 V; V _{GE} ≤ 20 V; T _j = 125 °C V _{CES} < 1200 V		10	µs
Inverse Diode				
I _F	T _j = 150 °C	T _s = 25 °C	57	A
		T _s = 80 °C	38	A
I _{FRM}	I _{FRM} = 2 x I _{Fnom}			A
I _{FSM}	t _p = 10 ms; half sine wave T _j = 150 °C		550	A
Module				
I _{t(RMS)}				A
T _{vj}			-40 ... +150	°C
T _{stg}			-40 ... +125	°C
V _{isol}	AC, 1 min.		2500	V

Characteristics		$T_s = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 2\text{ mA}$	4,5	5,5	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$		0,2	0,1	mA
					mA
I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$			200	nA
					nA
V_{CE0}			1,1	1,3	V
				1,2	V
r_{CE}	$V_{GE} = 15\text{ V}$		16		$\text{m}\Omega$
				18	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 50\text{ A}, V_{GE} = 15\text{ V}$	1,7	$T_j = 25^\circ\text{C}_{chiplev.}$	2,3	V
			$T_j = 125^\circ\text{C}_{chiplev.}$	2,3	V
C_{ies}	$V_{CE} = 25, V_{GE} = 0\text{ V}$		4,46		nF
C_{oes}			0,33		nF
C_{res}			0,21		nF
$t_{d(on)}$	$R_{Gon} = 15\ \Omega$		80		ns
t_r			50		ns
E_{on}	$R_{Goff} = 15\ \Omega$		$V_{CC} = 600\text{V}$ $I_C = 50\text{A}$	5,8	mJ
$t_{d(off)}$			$T_j = 125^\circ\text{C}$	420	ns
t_f			$V_{GE} = \pm 15\text{V}$	40	ns
E_{off}				4,8	mJ
$R_{th(j-s)}$	per IGBT			0,6	K/W



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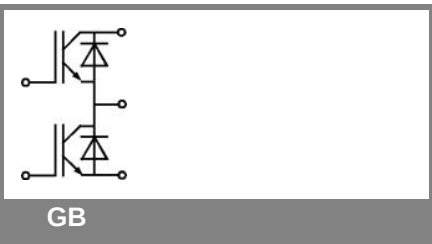
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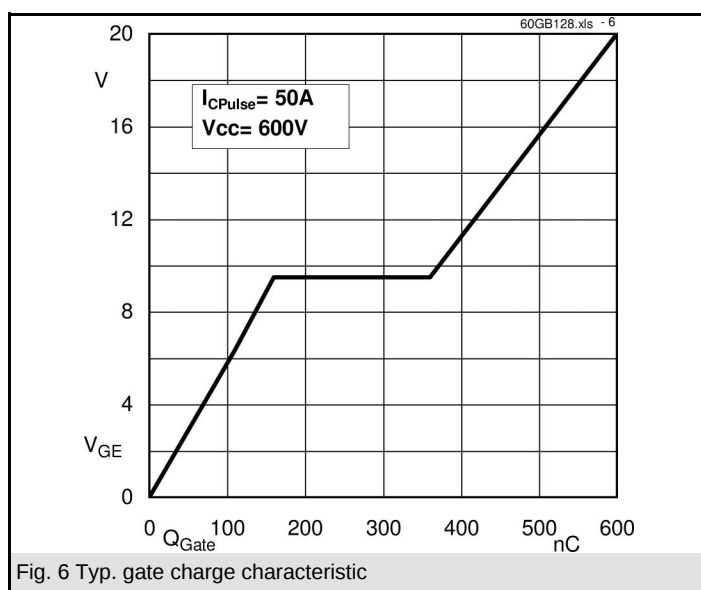
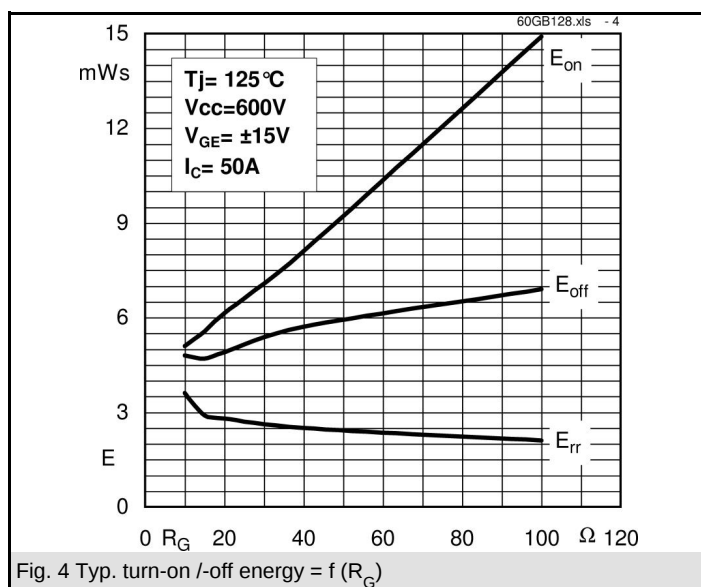
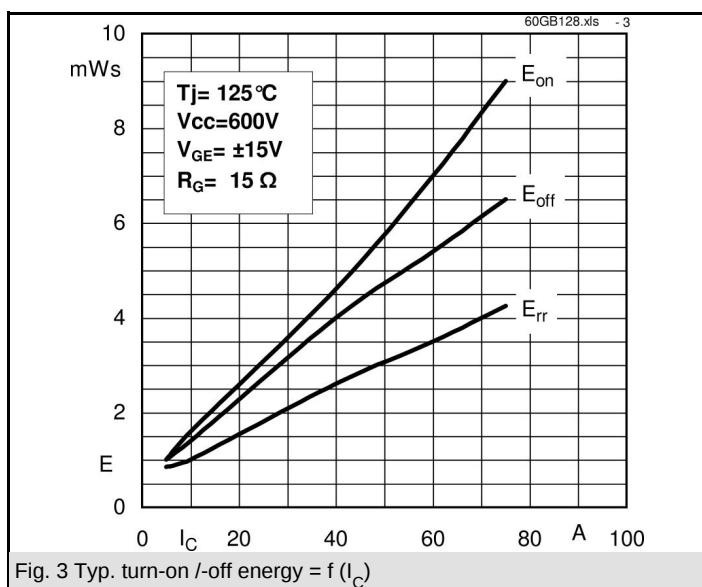
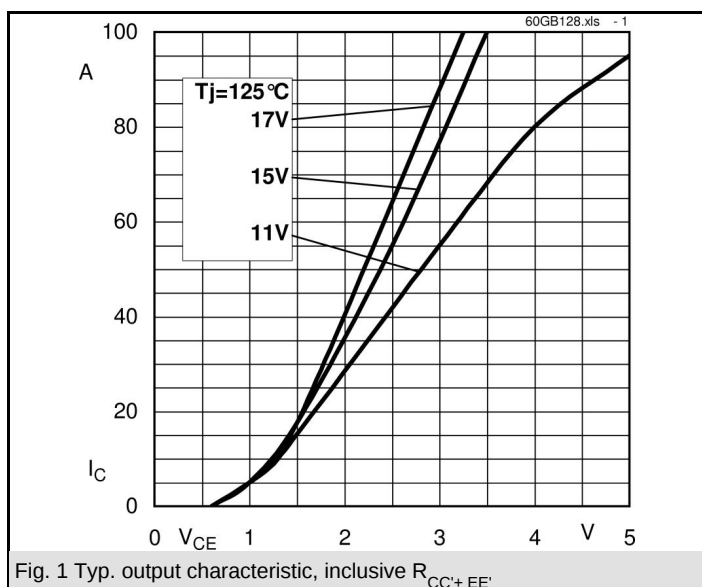
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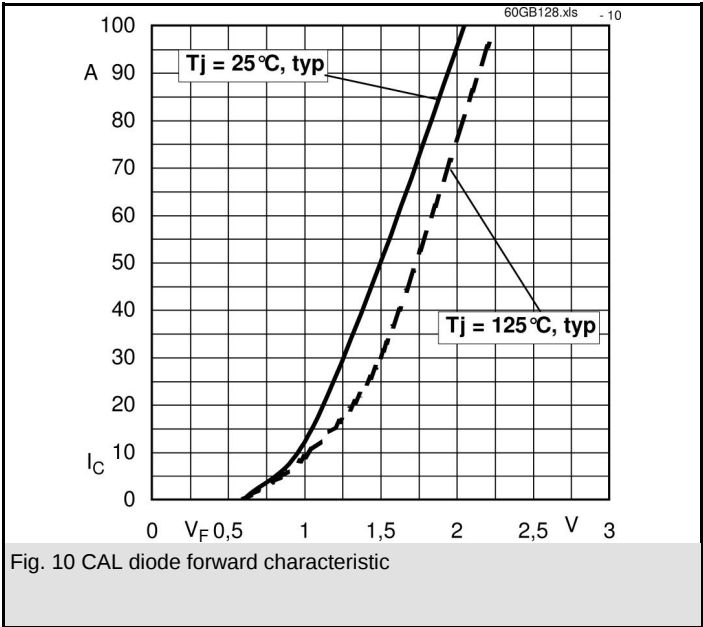
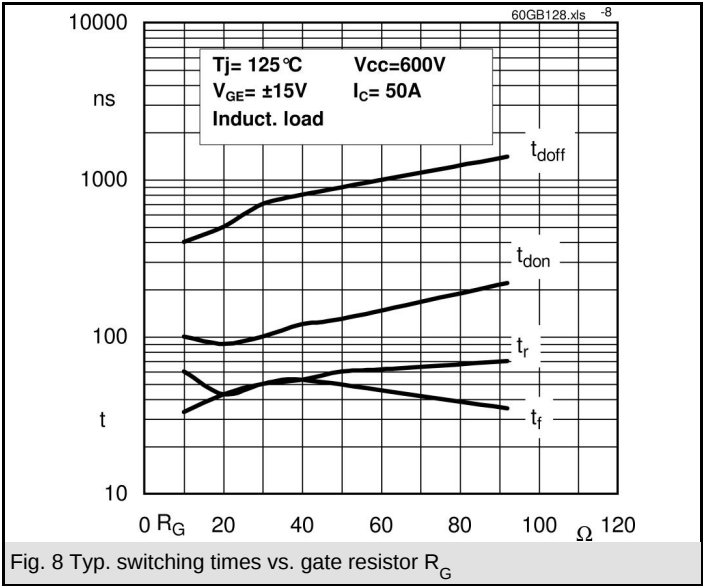
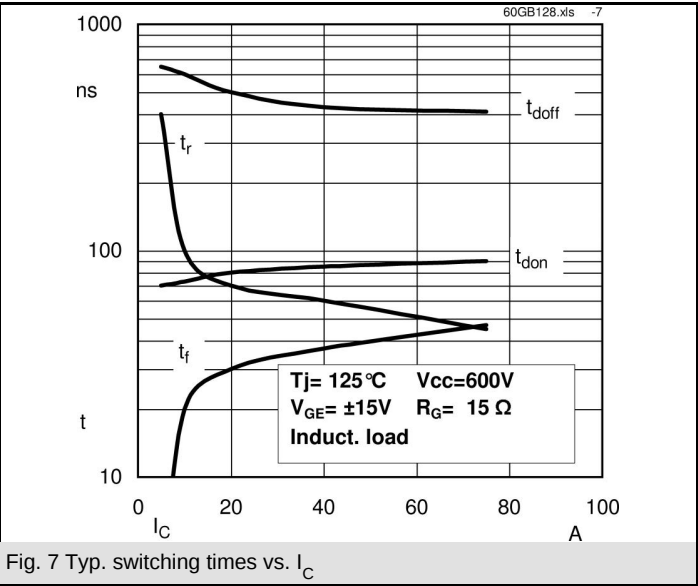


Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 50\text{ A}; V_{GE} = 0\text{ V}$		$T_j = 25\text{ }^{\circ}\text{C}_{chiplev.}$	2	V
			$T_j = 125\text{ }^{\circ}\text{C}_{chiplev.}$	1,8	V
V_{F0}			$T_j = 125\text{ }^{\circ}\text{C}$	1	V
r_F			$T_j = 125\text{ }^{\circ}\text{C}$	18	mΩ
I_{RRM}	$I_F = 50\text{ A}$ $di/dt = -800\text{ A/}\mu\text{s}$ $V_{CC} = 600\text{ V}$		$T_j = 125\text{ }^{\circ}\text{C}$	40	A
Q_{rr}				8	μC
E_{rr}				2	mJ
$R_{th(j-s)D}$	per diode			0,9	K/W
M_s	to heat sink M1	2,25		2,5	Nm
w			29		g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

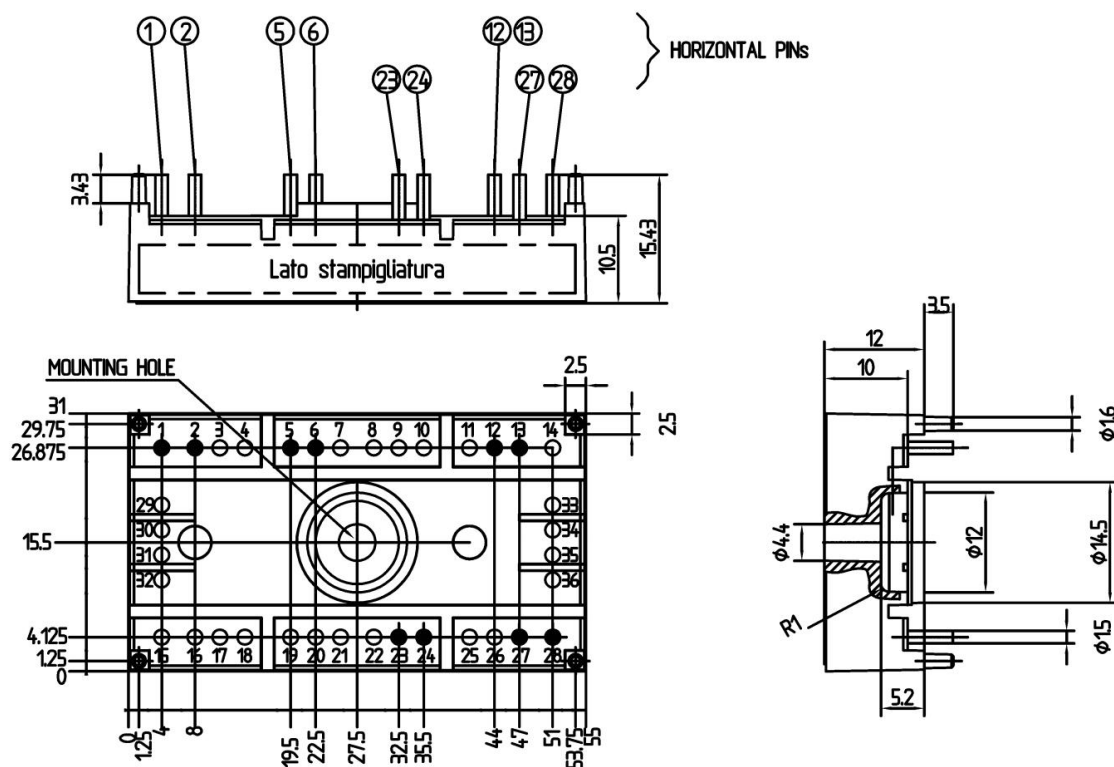
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



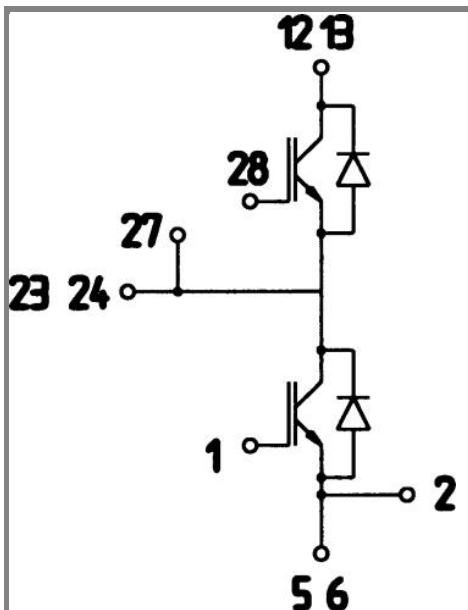


UL recognized file

no. E 63 532



Case T27 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T27

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